

AMENDMENTS IN THE SPECIFICATION:

Please amend paragraph [0017] in the specification as follows:

[0017] In the solid-state imaging apparatus according to the present invention, ~~the electroconductive member provided so as to cover at least the pn junction portions exposed on one side of the semiconductor substrate is connected to the fixed potential, or is grounded, and thus the charge generated in the region except for the photodiodes is discharged through the electroconductive member to the outside, without being accumulated in the pn junction portions.~~ For this reason, it is feasible to suppress the occurrence of the interface leak of charge in the pn junction portions and thereby prevent the deterioration of the SN ratio.